

# AVX TPS Series III

## NEXT GENERATION LOW ESR MnO<sub>2</sub> CAPACITORS

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## INTRODUCTION

One common trend in switch-mode power supply, micro-processor, and digital circuit applications is to achieve reduced noise while operating at higher frequencies. In order to realize this, components with low Equivalent Series Resistance (ESR), high capacitance and high reliability are required. A new generation of Low ESR tantalum chip capacitors has been developed by AVX utilizing a low resistivity MnO<sub>2</sub> electrolyte that enables very low component ESR. MnO<sub>2</sub> technology provides excellent field performance, environmental stability and high electrical and thermal stress resistance in wide voltage range from four to thirty-five volts. The capacitors are designed for operation in temperatures up to 125°C.

## REQUIREMENTS

Tantalum capacitor technology has many characteristics ideal for filtering applications in DC/DC converters, power supplies and other applications. The most important and common characteristics are:

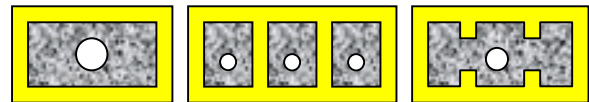
- Low and Stable ESR
- High Capacitance Retention at High Frequencies
- Low Failure Rate
- Wide Voltage Range
- Surge Robustness
- Environment (moisture/temperature) Resistant
- Low Cost

The above features were taken as the development criteria for the new AVX TPS Series III of very low ESR capacitors. MnO<sub>2</sub> technology in conjunction with tantalum dielectric is best suited to meet all of these the criteria including low ESR, excellent stability, reliability and wide voltage range.

## DESIGN FOR VERY LOW AND STABLE ESR

### Anode Shape

The overall surface area of a tantalum capacitor anode, particularly its surface-to-volume ratio, is one of the key parameters that defines its ESR value - the higher the overall surface area, the lower the ESR.



a) single anode    b) multi anode    c) fluted anode

*Figure.1. Anode design in cross section*

The single anode (Figure 1a) is the standard used for general capacitor designs because of cost and performance efficiency. A multi-anode design (Figure 1b) offers the lowest possible ESR [1,2]; however it is a more costly solution. Apart from additional manufacturing steps (e.g. multiple internal welds), there is also a production yield impact. If the standard yield for single anode (the active capacitor element) is ~ 90%, then the total yield for three anodes in a single

assembly is  $\sim 0.9 \times 0.9 \times 0.9 = 73\%$ , entailing higher cost compared to a single anode solution. The fluted anode design (Figure 1.c) using standard chip assembly processes was selected for New TPS Series III design as the optimum compromise between low ESR and cost requirements. The flute design has been developed by AVX engineers and introduced to mass production six years ago in order to achieve very low ESR on TPS series.

### MnO<sub>2</sub> Conductivity

Much experimental research has focused on improving the MnO<sub>2</sub> conductivity by optimising pyrolysis conditions [3, 4]. This has resulted in significant overall ESR reduction. While process design of experiments can optimise ESR, the basic physics behind conductivity processes in MnO<sub>2</sub> was not fully understood. This led to the conclusion that ESR levels below 50mΩ for tantalum capacitors could only be achieved by either conductive polymer or multi-anode solutions.

Current research in co-operation with Czech Noise Research Laboratory of Brno University of Technology suggests that the capability for MnO<sub>2</sub> to achieve high conductivity in tantalum capacitors has been underestimated. Now, based on a better understanding of the physical mechanisms involved, we are able to demonstrate that ESR values can be significantly improved by modification of MnO<sub>2</sub> technology in accordance with the energy level diagram shown below:

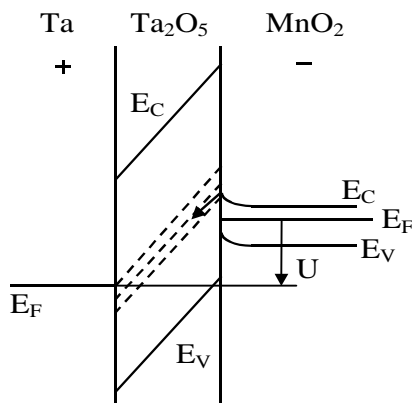


Figure 2. Band diagram of tantalum capacitor in normal mode

A tantalum capacitor can be represented by MIS hetero-structure with N-type MnO<sub>2</sub> semiconductor having a band diagram, as illustrated in Figure 2 (see also Figure 5). In this model, MnO<sub>2</sub>:β phase has a band gap of 0.26 eV and MnO<sub>2</sub>:γ phase 0.58-0.7 eV. When an ideal MIS structure is biased, three cases may exist at the semiconductor surface: the accumulation of carriers near the semiconductor surface, depletion of carriers and carrier inversion. These parameters are also

dependent on bulk conductivity, carrier concentration (typically  $10^{19} \text{ cm}^{-3}$  with mobility  $(1-3) \Omega \text{ cm}^2/\text{Vs}$ ), and surface charge density or surface potential (also a function of MnO<sub>2</sub> crystals surface morphology). The volume of MnO<sub>2</sub> and its crystals surface potential depend on temperature. Conductivity (ESR) increases with temperature and humidity. Both the morphology /structure and conductivity of MnO<sub>2</sub> crystals are crucial to ESR improvement. The interfaces between Ta - Ta<sub>2</sub>O<sub>5</sub> and Ta<sub>2</sub>O<sub>5</sub> - MnO<sub>2</sub> are also important to consider for ESR versus frequency characteristics.

Figure 3 is a comparison of typical ESR values at 100kHz for conventional TPS and Series III TPS.

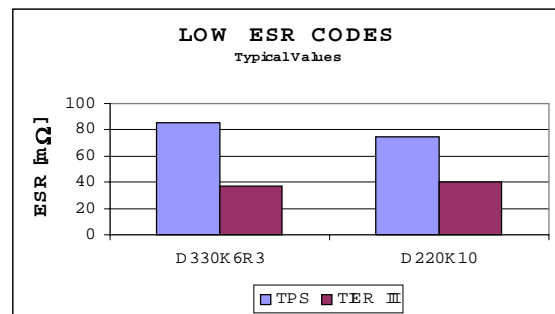


Figure 3. Conventional TPS vs Tier III typical ESR value

### ESR, Capacitance vs frequency, Higher Ripple Load

The ESR improvements resulting from the new Low ESR Series III technology can be seen over whole frequency range from 100Hz up to the capacitor's self-resonance frequency. A comparison of a conventional TPS low ESR capacitor D case 100μF 10V with 100mΩ ESR, a new TPS Series III D case 100μF 10V with 50mΩ ESR and a conductive polymer D100μF 10V with 55mΩ ESR are shown in Figure 4.

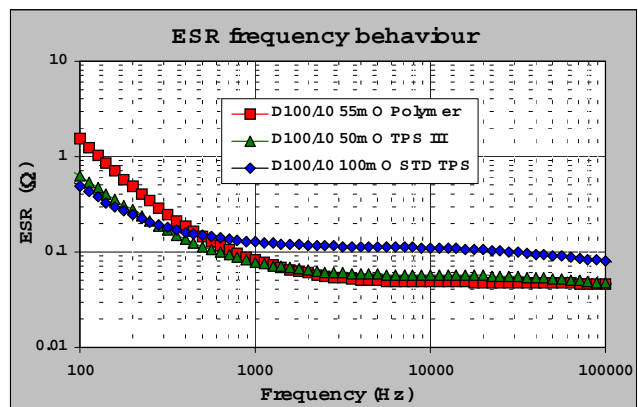


Figure 4. TPS, TPS III and Polymer ESR vs. frequency

Lower ESR in tantalum capacitors is also associated with lower capacitance loss with frequency and higher continuous ripple current ratings [1]. These effects depend on the actual ESR level, and are of the

technology employed. Hence, for example, D case capacitors having a 100kHz ESR of 50mΩ made with MnO<sub>2</sub> or conductive polymer materials will show about the same capacitance loss with frequency and have equivalent ripple current ratings (power dissipation for a moulded D case part is essentially independent of the electrolyte technology used). The capacitance loss over frequency for the same group of parts as above is shown in Figure 5, and a ripple current comparison is shown in Fig.6.

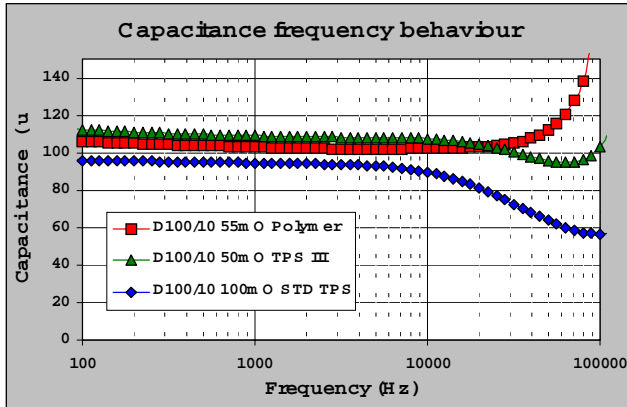


Figure 5. TPS, TPS III and Polymer Cap vs frequency

series	Part Number	Ripple Current (mA) @100kHz		
		25°C	85°C	125°C
conventional TPS	TPSD107K010R0100	125	110	49
TPS Series III	TPSD107K010R0050	173	159	63

Figure 6. TPS and TPS III Ripple Current Comparison

#### Temperature Dependence of ESR

The temperature behaviour of ESR for new TPS III capacitors, as compared to conventional low ESR tantalum and polymer tantalum capacitors is shown in Figure 7.

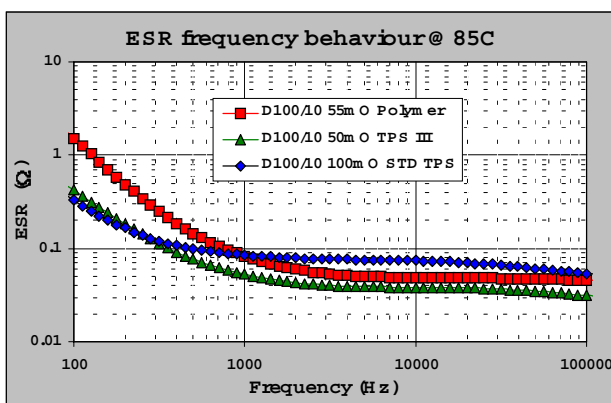


Figure 7. TPS, TPS III and Polymer vs frequency @85°C

The conductivity of MnO<sub>2</sub> increases as temperature increases. When used as the counter-electrode material in tantalum capacitors, this gives lower ESR as temperature increases. This is a significant difference to the ESR characteristic of polymer counter-electrode

systems, which do not have increased conductivity. This is an important consideration in applications with higher operating temperature.

#### Graphite and Silver Counter-electrode Materials

Graphite and silver polymeric materials are used as part of the outer counter-electrode layers. The self-resistance and contact resistance of these materials also has a significant effect on the overall ESR and ESR stability (see Figure 6). It can be expected that interface resistance between MnO<sub>2</sub> and graphite is also dependent on the material formulation and how it is applied. Close co-operation and strategic relationship between AVX and manufacturers of these materials has resulted in an improved materials system for the new TPS series III to maintain a low and stable ESR under various humidity and high temperature conditions.

Highly accelerated tests were used to evaluate ESR stability. Standard TPS and TPS Series III units were subjected to a 1<sup>st</sup> reflow cycle, then subjected to a pressure cooker test (two hours humidity exposure at two atmospheres pressure at 120°C) followed by a 2<sup>nd</sup> exposure to reflow. The results on TPSD337\*006 (D case 330µF 6.3V) are shown in Figure 8.

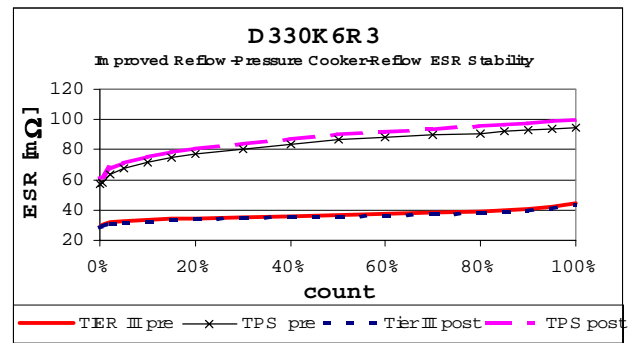


Figure 8. D330µF 6.3V ESR stability after pressure cooker / reflow test.

#### SURGE ROBUST

##### Active Surge Load Suppression

Following the improvements made in the graphite and silver materials, humidity and stress absorption barriers were also evaluated in the new TPS Series III design. The role of these barriers is to absorb any mechanical stresses that can occur (typically during pcb manufacture) as well as electrical stresses (typically in low impedance circuits such as in power supply applications).

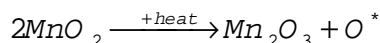
##### Advanced Surge Testing

An intelligent dynamic surge test has been developed by AVX engineers based on observations of thermal runaway in overloading conditions – see CARTS published papers 7],8]. The new TPS Series III is 100% surge screened using this system during production.

## LOW FAILURE RATE and DCL

### Efficient Self-Healing

Tantalum capacitors are well known for good reliability characteristics, no dielectric wear-out mechanism and decreasing failure rate with time under steady state conditions. The self-healing process of MnO<sub>2</sub> is responsible for this behaviour. Current flowing through a defect site in Ta<sub>2</sub>O<sub>5</sub> dielectric heats MnO<sub>2</sub> at the interface. At temperatures about 400°C, the conductive semiconductor MnO<sub>2</sub> will change to Mn<sub>2</sub>O<sub>3</sub>, a material having much higher resistivity. This process can isolate the failure site and self-heal the capacitor.



Mobile oxygen atoms, a side product of this reaction, are also an important element in the self-healing process of MnO<sub>2</sub> tantalum capacitors. This oxygen is responsible for decreasing failure rate with time as it continually dopes the Ta<sub>2</sub>O<sub>5</sub> dielectric and maintains its dielectric features. There are self-healing mechanisms known for different technologies such as aluminium, plastic film and polymeric capacitors; however the decreasing failure rate with time is solely a characteristic of the traditional MnO<sub>2</sub> tantalum capacitor system.

Larger concentrations of oxygen produced by self-healing during high surge overload can however result in thermal runaway of the capacitor. Hence, surge limitation and/or appropriate derating is recommended for low impedance applications to protect the capacitor against overload (see Figure 9).

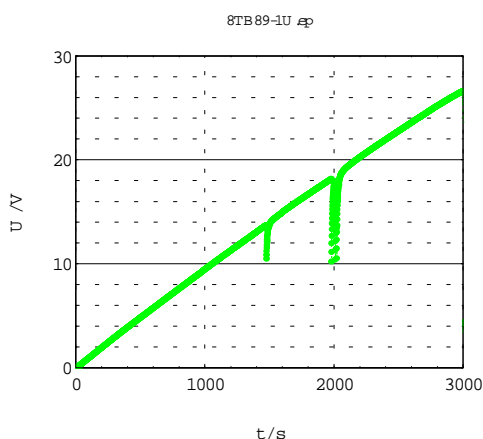


Figure 9. Self healing effect on 10V MnO<sub>2</sub> capacitor

During overload, the internal thermal impedance of the tantalum anode is important in providing good surge robustness of these very low ESR parts; in TPS series III, a special mix of tantalum particle sizes is used to enable greater internal heat dissipation and ensure no

“weak links” occur as thermal runaway paths are generated.

A simple test that can be reproduced in any basic laboratory can demonstrate the high efficiency of the self-healing process in tantalum capacitors with MnO<sub>2</sub> counter-electrode. A ramp voltage source is applied to the capacitor with small voltage increments to initiate electrical breakdown of the dielectric, but not to cause thermal overloading. An optional resistor (1kΩ) can be added for better current limitation and faster voltage step-up change. It is possible to see the first breakdown at a voltage approximately 40% higher than the rated voltage. High current will start to flow through the capacitor and generate the self-healing reaction that repairs the failure site and the capacitor leakage will return to normal. Two breakdowns at 14v and 18v were recorded in a 10v rated capacitor with subsequent self-healing – see Figure 9. This effective self-healing process is unique to MnO<sub>2</sub> tantalum capacitor technology only and unlike any other technology / component self-repairing reactions like conductive polymer.

### Low Leakage Current (DCL)

The general specification for leakage current of tantalum MnO<sub>2</sub> capacitor ratings is 0.01xCV (0.01 x capacitance x voltage rating) equation. For example, 100μF 10V capacitor will have 10μA DCL specification limit. The same capacitor with conductive polymer has a ten times higher DCL limit at 100μA. The difference in leakage current between these two technologies is possible to explain by the different work functions of MnO<sub>2</sub> and CP (conductive polymer) materials. This can be understood by reference to the MIS structure (see e.g. 5)

## WIDE VOLTAGE RANGE

The new TPS Series III comprises a full voltage range from four to thirty five volts, as with most MnO<sub>2</sub> technologies. This series provides the lowest ESR available for high voltage parts – especially 25v and 35v ratings demanded by Power Supply applications show the LOWEST ESR in the industry.

## WIDE TEMPERATURE RANGE

Wide temperature range operation is one of the additional requirements of power converter designers. Series III is specified within operating temperatures from -55°C up to +125°C in accordance to working range of MnO<sub>2</sub> capacitors. This range allows standard operation at higher temperatures (125°C) compare to the current polymer solutions on diverse capacitor technologies e.g. tantalum and aluminium (usually +105°C maximum).

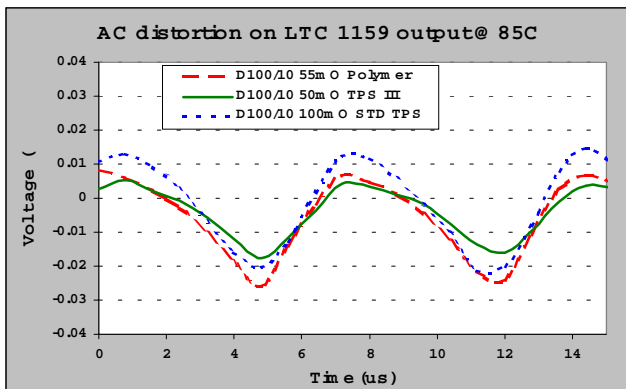
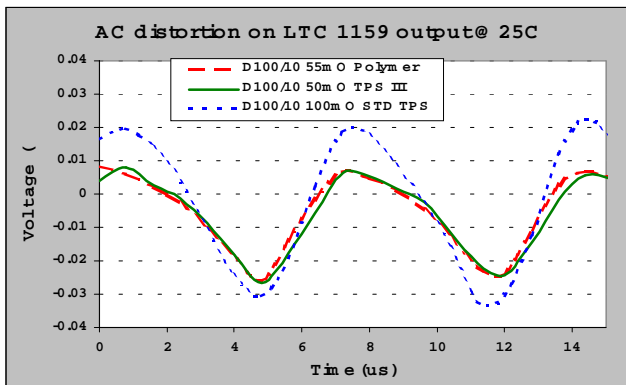
## Application Test

An application experiment was performed in order to compare filtering abilities of the conventional TPS capacitor D case 100 $\mu$ F 10V 100m $\Omega$  rating, the new TPS Series III D case 50m $\Omega$  and conductive polymer 55m $\Omega$  ratings. The evaluation used a Linear Technology switching regulator (LTC1159) with a 10v input and 3.3v output rail at 3.3 $\Omega$  load – see Figure 10.



Figure 10. LTC1159 test board picture

The output ripple current with a single capacitor on the output was recorded at operating temperatures of 25 $^{\circ}$ C and 85 $^{\circ}$ C to evaluate the filtering abilities of conductive polymer, TPS and TPS III series. (The LT specification recommends two D case 100 $\mu$ F 10v 100m $\Omega$  capacitors). – see Figures 11 and 12 below.



Figures 11,12. AC distortion output on LTC1159

Comparable values of output ripple distortion were measured with TPS III and Polymer capacitors on the output at 25 $^{\circ}$ C. There is no surprise that the standard TPS with twice the ESR value shows worse output ripple distortion. But significantly, the output ripple noise drops to its lowest in the case of the TPS III capacitor at the higher operating temperature (85 $^{\circ}$ C) when compared to the conductive polymer capacitor. This is in-line with ESR versus temperature behaviour discussed previously in this paper.

## Specification of New TPS Series III

Case Sizes: C, D, E, Y, W

Capacitance: 10 $\mu$ F – 330 $\mu$ F (470 $\mu$ F\*)

Voltage: 6v – 35v (50v\*)

Temperature range: -55 $^{\circ}$ C/+125 $^{\circ}$ C

ESR limit: 45 (6/10v) – 150 (35v) m $\Omega$

(Half the limit of the conventional TPS)

\* - under development

## CONCLUSION

The new TPS Series III of super low ESR tantalum capacitors with MnO<sub>2</sub> was designed based on long-term teamwork of experienced people from University, Technology, Production, Purchasing, Quality and Marketing. ESR values half that of the original TPS series were achieved while retaining all the advantages of mature MnO<sub>2</sub> capacitor technology. The Series III technology is applicable to a whole voltage range of today's MnO<sub>2</sub> parts. The TPS Series III matrix is quickly being expanded to meet demands from a wide range of potential applications. All technology modifications were carefully examined against COST FOR PERFORMANCE criteria before implemented to this New Low ESR Series III project.

	MnO <sub>2</sub> technology		Conductive Polymer		
	conventional	<b>Series III</b>	Supplier 1.	Supplier 2	Supplier 3
<b>voltage range [V]</b>	<b>4 - 50V</b>	<b>4 - 50V</b>	4 - 10V	2.5 - 16V	4 - 10V
<b>maximum capacitance [uF]</b>	<b>1000 uF</b>	<b>1000 uF</b>	470uF	680uF	330uF
<b>tightest capacitance tolerance [ +/- %]</b>	<b>10%</b>	<b>10%</b>	20%	20%	20%
<b>ESR (D100/10) [mO]</b>	100mO	<b>50mO</b>	<b>55mO</b>	<b>55mO</b>	<b>55mO</b>
<b>DF (D100/10) [%]</b>	<b>8%</b>	<b>8%</b>	10%	10%	30%
<b>DCL (D100/10) [uA]</b>	<b>10uA</b>	<b>10uA</b>	100uA	100uA	100uA
<b>ripple current (D100/10) [Arms]</b>	1.2	<b>1.7</b>	<b>1.7</b>	1.5	1.5
<b>temperature range [C]</b>	<b>-55/+125</b>	<b>-55/+125</b>	-55/+105	-55/+105	-55/+105

\* - under development

August 2001

**BOLD = superior specification**

Figure 13. Generic specification comparison of TPS, TPS Series III and conductive polymer technology

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- 4] G.Winkler, J.Gerblinger, M.Brenner, "Lowest and Stable ESR Values of Tantalum Capacitors with Improved Standard Technologies", CARTS Europe 1999 Lisboa, Portugal, pp.79-84
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- 7] P.Vasina, T.Zednicek, J.Sikula, J.Pavelka, "Thermal and Electrical Breakdown Versus Reliability of Ta<sub>2</sub>O<sub>5</sub> Under Both-Bipolar Biasing Conditions" CARTS EUROPE 2000, Brussels, Belgium, pp 89-93
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# APPENDIX 1. TPS SERIES MATRIX

SERIES MATRIX (ESR values in brackets [in  $\Omega$ ])

update: 23.10.2001

Capacitance	Rated Voltage DC (VR) to 85°C							
$\mu\text{F}$	4V	6.3V	10V	16V	20V	25V	35V	50V
4.7								D(300)
6.8								
10							D(125)	
15						D(100,125)	D(125)	
22					C(150)	D(125)	D(125,200)/E(125)	
33			C(150)	W(150,250)	D(100)	D(100) E(100,125)	D(200)/E(125)	
47		B(250)	W(125,150,250)	D(80)	D(100) E(100,125)	E(125) E(100)	V(100)	
68		W(100,125,200)	Y(70,100)	D(70)	D/E(100)	E(125)		
100	D(40,50)	C(75) Y(65,100)	C(75),D(50) Y(65,100)	Y(65,100) D/E(55) E(65)	V(60)			
150	D(40,50)	D(50)	Y(65,100) D(50)	E/V(50)				
220	D(40,50)	D(50)	D(50), E(50)	V(45,50)				
330	D(40,50)	D(45,50)	E(45,50)					
470	D(45) E(40)	E/V(45) V(35,40)	E(45)					
680	E(40)	E(45), V(35,40)						
1000	V(35), E(40) V(40)							

blue released

black engineering samples

red underdevelopment

Issue 3.0

Code	EIA Code	L $\pm$ 0.2 (0.008)	W+0.2 (0.008) -0.1 (0.004)	H+0.2 (0.008) -0.1 (0.004)	W1 $\pm$ 0.2 (0.008)	A+0.3 (0.012) -0.2 (0.008)	S Min.
B	3528	3.5 (0.138)	2.8 (0.110)	1.9 (0.075)	2.2 (0.087)	0.8 (0.031)	1.4 (0.055)
C	6032	6.0 (0.236)	3.2 (0.126)	2.6 (0.102)	2.2 (0.087)	1.3 (0.051)	2.9 (0.114)
D	7343	7.3 (0.287)	4.3 (0.169)	2.9 (0.114)	2.4 (0.094)	1.3 (0.051)	4.4 (0.173)
E	7343H	7.3 (0.287)	4.3 (0.169)	4.1 (0.162)	2.4 (0.094)	1.3 (0.051)	4.4 (0.173)
V	7361	7.3 (0.287)	6.1 (0.240)	3.45 $\pm$ 0.3 (0.136 $\pm$ 0.012)	3.1 (0.120)	1.4 (0.055)	4.4 (0.173)
W*	6032L	6.0 (0.236)	3.2 (0.126)	1.5 (0.059) max.	2.2 (0.087)	1.3 (0.051)	2.9 (0.114)
Y**	7343L	7.3 (0.287)	4.3 (0.169)	2.0 (0.079) max.	2.4 (0.094)	1.3 (0.051)	4.4 (0.173)

W1 dimension applies to the termination width for A dimensional area only.  
 \* Low Profile Version of C Case (max. height 1.5mm)  
 \*\* Low Profile Version of D Case (max. height 2mm)

# APPENDIX 2. TPS SERIES III SPECIFICATION TABLE

Ratings and Part Number Reference

AVX Part No.	Case Size	Capacitance $\mu$ F	Rated Voltage (V)	DCL (uF) Max.	DF % Max. @ 100kHz	ESR Max. (m Ohm) @ 100kHz	100kHz Ripple Current (mA) Ratings			100kHz Ripple Voltage (mV) Ratings		
							25°C	85°C	125°C	25°C	85°C	125°C
TPSD107*004#0040	D	100	4	4	6	40	1936	1743	775	77	70	31
TPSD107*004#0050	D	100	4	4	6	50	1732	1559	693	87	78	35
TPSD157*004#0040	D	150	4	6	6	40	1936	1743	775	77	70	31
TPSD157*004#0050	D	150	4	6	6	50	1732	1559	693	87	78	35
TPSD227*004#0040	D	220	4	8.8	8	40	1936	1743	775	77	70	31
TPSD227*004#0050	D	220	4	8.8	8	50	1732	1559	693	87	78	35
TPSD337*004#0040	D	330	4	13.2	8	40	1936	1743	775	77	70	31
TPSD337*004#0050	D	330	4	13.2	8	50	1732	1559	693	87	78	35
TPSD477*004#0045	D	470	4	18.8	12	45	1826	1643	730	82	74	33
TPSE477*004#0040	E	470	4	18.8	10	40	2031	1828	812	81	73	32
TPSE687*004#0040	E	680	4	27.2	14	40	2031	1828	812	81	73	32
TPSE108*004#0040	E	1000	4	40.0	14	40	2031	1828	812	81	73	32
TPSV108*004#0035	V	1000	4	40.0	16	35	2673	2405	1069	94	84	37
TPSV108*004#0040	V	1000	4	40.0	16	40	2500	2250	1000	100	90	40
TPSB476*006#0250	B	47	6.3	3.0	6	250	583	525	233	146	131	58
TPSW 686*006#0100	W	68	6.3	4.3	6	100	949	854	379	95	85	38
TPSW 686*006#0125	W	68	6.3	4.3	6	125	849	764	339	106	95	42
TPSW 686*006#0200	W	68	6.3	4.3	6	200	671	604	268	134	121	54
TPSC107*006#0075	C	100	6.3	6.3	6	75	1211	1090	484	91	82	36
TPSY107*006#0065	Y	100	6.3	6.3	6	65	1387	1248	555	90	81	36
TPSY107*006#0100	Y	100	6.3	6.3	6	100	1118	1006	447	112	101	45
TPSD157*006#0050	D	150	6.3	9.5	6	50	1732	1559	693	87	78	35
TPSD227*006#0050	D	220	6.3	13.9	8	50	1732	1559	693	87	78	35
TPSD337*006#0050	D	330	6.3	20.8	8	50	1732	1559	693	87	78	35
TPSD337*006#0045	D	330	6.3	20.8	8	45	1826	1643	730	82	74	33
TPSE477*006#0045	E	470	6.3	29.6	10	45	1915	1723	766	86	78	34
TPSV477*006#0035	V	470	6.3	29.6	10	35	2673	2405	1069	94	84	37
TPSV477*006#0040	V	470	6.3	29.6	10	40	2500	2250	1000	100	90	40
TPSV477*006#0045	V	470	6.3	29.6	10	45	2357	2121	943	106	95	42
TPSV687*006#0035	V	680	6.3	42.8	14	35	2673	2405	1069	94	84	37
TPSV687*006#0040	V	680	6.3	42.8	14	40	2500	2250	1000	100	90	40
TPSE687*006#0045	E	680	6.3	42.8	10	45	1915	1723	766	86	78	34
TPSC336*010#0150	C	33	10	3.3	6	150	856	771	343	128	116	51
TPSW 476*010#0125	W	47	10	4.7	6	125	849	764	339	106	95	42
TPSW 476*010#0150	W	47	10	4.7	6	150	775	697	310	116	105	46
TPSW 476*010#0250	W	47	10	4.7	6	250	600	540	240	150	135	60
TPSY686*010#0070	Y	68	10	6.8	6	70	1336	1203	535	94	84	37
TPSY686*010#0100	Y	68	10	6.8	6	100	1118	1006	447	112	101	45
TPSC107*010#0075	C	100	10	10.0	8	75	1211	1090	484	91	82	36
TPSD107*010#0050	D	100	10	10.0	6	50	1732	1559	693	87	78	35
TPSY107*010#0065	Y	100	10	10.0	6	65	1387	1248	555	90	81	36
TPSY107*010#0100	Y	100	10	10.0	6	100	1118	1006	447	112	101	45
TPSD157*010#0050	D	150	10	15.0	6	50	1732	1559	693	87	78	35
TPSY157*010#0065	Y	150	10	15.0	6	65	1387	1248	555	90	81	36
TPSY157*010#0100	Y	150	10	15.0	6	100	1118	1006	447	112	101	45
TPSD227*010#0050	D	220	10	22.0	8	50	1732	1559	693	87	78	35
TPSE227*010#0050	E	220	10	22.0	8	50	1817	1635	727	91	82	36
TPSE337*010#0045	E	330	10	33.0	8	45	1915	1723	766	86	78	34
TPSE337*010#0050	E	330	10	33.0	8	50	1817	1635	727	91	82	36
TPSE477*010#0045	E	470	10	47.0	10	45	1915	1723	766	86	78	34
TPSW 336*016#0150	W	33	16	5.3	6	150	775	697	310	116	105	46
TPSW 336*016#0250	W	33	16	5.3	6	250	600	540	240	150	135	60
TPSD476*016#0080	D	47	16	7.5	6	80	1369	1232	548	110	99	44
TPSD686*016#0070	D	68	16	10.8	6	70	1464	1317	586	102	92	41
TPSD107*016#0055	D	100	16	16.0	6	55	1651	1486	661	91	82	36
TPSE107*016#0055	E	100	16	16.0	6	55	1732	1559	693	95	86	38
TPSE107*016#0065	E	100	16	16.0	6	65	1593	1434	637	104	93	41
TPSY107*016#0065	Y	100	16	16.0	8	65	1387	1248	555	90	81	36
TPSY107*016#0100	Y	100	16	16.0	8	100	1118	1006	447	112	101	45
TPSE157*016#0050	E	150	16	24.0	6	50	1817	1635	727	91	82	36
TPSV157*016#0050	V	150	16	24.0	6	50	2236	2012	894	112	101	45
TPSV227*016#0045	V	220	16	35.2	8	45	2357	2121	943	106	95	42
TPSV227*016#0050	V	220	16	35.2	8	50	2236	2012	894	112	101	45
TPSC226*020#0150	C	22	20	4.4	6	150	856	771	343	128	116	51
TPSD336*020#0100	D	33	20	6.6	6	100	1225	1102	490	122	110	49
TPSD476*020#0100	D	47	20	9.4	6	100	1225	1102	490	122	110	49
TPSE476*020#0100	E	47	20	9.4	6	100	1285	1156	514	128	116	51
TPSE476*020#0125	E	47	20	9.4	6	125	1149	1034	460	144	129	57
TPSD686*020#0100	D	68	20	13.6	6	100	1225	1102	490	122	110	49
TPSE686*020#0100	E	68	20	13.6	6	100	1285	1156	514	128	116	51
TPSV107*020#0060	V	100	20	20.0	8	60	2041	1837	816	122	110	49
TPSD156*025#0100	D	15	25	3.8	6	100	1225	1102	490	122	110	49
TPSD156*025#0125	D	15	25	3.8	6	125	1095	986	438	137	123	55
TPSD226*025#0125	D	22	25	5.5	6	125	1095	986	438	137	123	55
TPSD336*025#0100	D	33	25	8.3	6	100	1225	1102	490	122	110	49
TPSE336*025#0100	E	33	25	8.3	6	100	1285	1156	514	128	116	51
TPSE336*025#0125	E	33	25	8.3	6	125	1149	1034	460	144	129	57
TPSE476*025#0100	E	47	25	8.3	6	100	1285	1156	514	128	116	51
TPSE476*025#0125	E	47	25	8.3	6	125	1149	1034	460	144	129	57
TPSE686*025#0125	E	68	25	17.0	6	125	1149	1034	460	144	129	57
TPSD106*035#0125	D	10	35	3.5	6	125	1095	986	438	137	123	55
TPSD156*035#0125	D	15	35	5.3	6	125	1095	986	438	137	123	55
TPSD226*035#0125	D	22	35	7.7	6	125	1095	986	438	137	123	55
TPSD226*035#0200	D	22	35	7.7	6	200	866	779	346	173	156	69
TPSE226*035#0125	E	22	35	7.7	6	125	1149	1034	460	144	129	57
TPSD336*035#0200	D	33	35	11.6	6	200	866	779	346	173	156	69
TPSE336*035#0125	E	33	35	11.6	6	125	1149	1034	460	144	129	57
TPSD476*035#0100	V	47	35	16.5	6	100	1581	1423	622	158	142	63
TPSD475*050#0300	D	47	50	2.4	6	300	707	636	283	212	191	85

All technical data relates to an ambient temperature of +25°C measured at 120Hz, 0.5V RMS unless otherwise stated.

\* Insert K for +10% and +20% tolerance of capacitance

# Insert R for 7" reel and S for 13" reel

**BLUE BOLT – RELEASED CODES**  
**RED CURSIV – UNDER DEVELOPMENT**

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